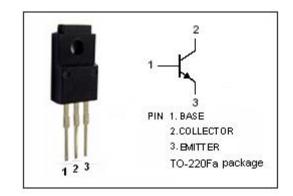


# **isc Silicon NPN Power Transistor**

### **DESCRIPTION**

- · Low Collector Saturation Voltage
- : V<sub>CE(sat)</sub>= 1.0V(Max)@ I<sub>C</sub>= 2A
- · Collector-Emitter Breakdown Voltage-
  - : V<sub>(BR)CEO</sub>= 80V (Min)
- · Wide Area of Safe Operation
- Complement to Type 2SA1635
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

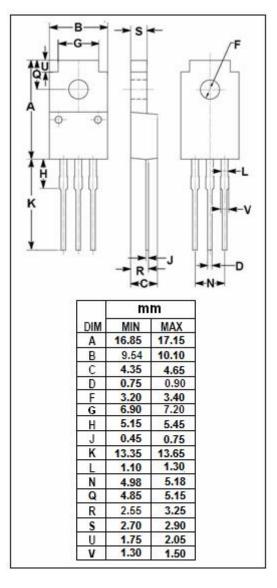


### **APPLICATIONS**

· Designed for audio and general purpose applications

# ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>CBO</sub>	Collector-Base Voltage	100	V	
V <sub>CEO</sub>	Collector-Emitter Voltage	80	V	
V <sub>EBO</sub>	Emitter-Base Voltage	6	V	
Ic	Collector Current-Continuous	4	А	
Ісм	Collector Current-Peak	6	А	
P <sub>C</sub>	Collector Power Dissipation @ T <sub>C</sub> =25°C	30	W	
	Collector Power Dissipation @ T <sub>a</sub> =25℃	2		
TJ	Junction Temperature 150		$^{\circ}$	
T <sub>stg</sub>	Storage Temperature Range	-55~150	$^{\circ}$	





# **isc Silicon NPN Power Transistor**

2SC4008

### **ELECTRICAL CHARACTERISTICS**

Tc=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = 50 μ A; I <sub>E</sub> = 0	100			V
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 25mA; I <sub>B</sub> = 0	80			V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 50 μ A; I <sub>C</sub> = 0	6			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 2A; I <sub>B</sub> = 0.2A			1.0	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	Ic= 2A; I <sub>B</sub> = 0.2A			1.5	V
Ісво	Collector Cutoff Current	V <sub>CB</sub> = 100V; I <sub>E</sub> = 0			10	μА
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 6V; I <sub>C</sub> = 0			10	μА
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 1A; V <sub>CE</sub> = 4V	100		500	
f⊤	Current-Gain—Bandwidth Product	I <sub>E</sub> = -0.2A ; V <sub>CE</sub> = 12V		10		MHz
Сов	Output Capacitance	I <sub>E</sub> =0 ; V <sub>CB</sub> = 10V; f <sub>test</sub> = 1MHz		60		pF

### ♦ h<sub>FE</sub> classifications

E	F	G
100-200	160-320	250-500

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